New Jersey Semi-Conductor Products, Inc.

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2N5832

Features

- Through Hole Package

Pin Configuration
Bottom View

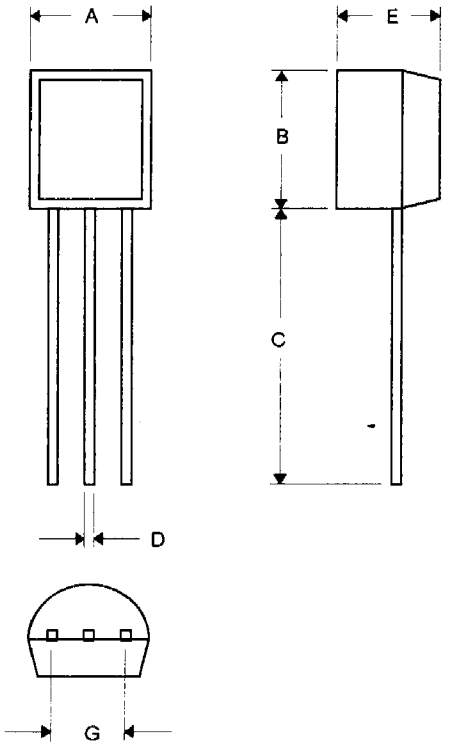
Plastic-case Bipolar NPN Transistor

Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (I_C=300mAdc)	140		Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	160		Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	5.0		Vdc
I_{CBO}	Collector-Base Breakdown Current (V_{CE}=120Vdc)		50	nAdc
ON CHARACTERISTICS				
h_{FE}	DC Current Gain* (I_C=10mAdc, V_{CE}=5.0Vdc)	175	500	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage (I_C=10mAdc)		0.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
f_T	Current Gain-Bandwidth Product (I_C=10mAdc)	100		MHz
C_{ob}	Output Capacitance		4.0	pF
NF	Noise Figure		----	dB

Note: Maximum at typical JEDEC condition
$V_{(BR)CER}$ @ R=10 OHMS

TO-92



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	